

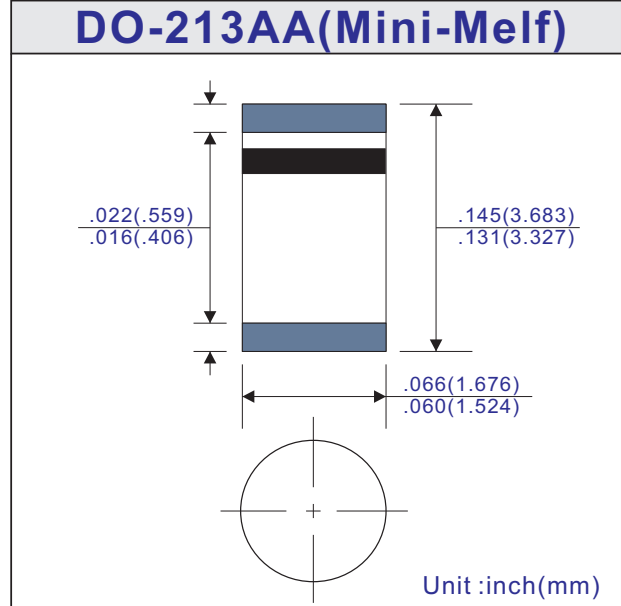


**0.5A Glass Passivated Surface Mount
 Hi-Efficiency Rectifiers - 50V to 1000V**



FEATURES
<ul style="list-style-type: none"> • Low drop down voltage • Ultrafast switching for high efficiency • High current capability • High surge current capability • Glass passivated chip junction • Surface mounted applications in order to optimize board space • Lead-free parts for green partner

MECHANICAL DATA
<ul style="list-style-type: none"> • Case: Molded plastic DO-213AA • Epoxy: UL94-V0 rated flame retardant • Terminals: Solderable per MIL-STD-750 Method 2026 • Polarity: Color band denotes cathode end • Mounting Position: Any • Weight: 0.0014 ounces, 0.036 grams



MAXIMUM RATING AND ELECTRICAL CHARACTERISTICS										
Ratings at 25°C ambient temperature unless otherwise specified										
	EGL-	Symbols	34A	34B	34D	34G	34J	34K	34M	Units
Maximum Recurrent Peak Reverse Voltage		VRRM	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage		VRMS	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage		VDC	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Current See Figure 1		I(AV)	0.5							Amps
Peak Forward Surge Current 8.3mS single half sine-wave superimposed on rated load (JEDEC Method) TL=110°C		IFSM	10.0							Amps
Maximum Instantaneous Forward Voltage at 0.5A		VF	1.0		1.3		1.7			Volts
Maximum DC Reverse Current at Rated DC Blocking Voltage		IR			5.0		100.0			µA
Typical Reverse Recovery Time (Note 1)		Trr	50			75			nS	
Typical Junction Capacitance (Note 2)		CJ	7.0							pF
Typical Thermal Resistance (Note 3)		RθJA RθJT					150 70		°C/W	
Operating Junction Temperature Range		TJ	-55 ~ +150							°C
Storage Temperature Range		TSTG	-55 ~ +150							°C

Note 1. Measured with If=0.5A, Ir=1A, IRR=0.25A
 2. Measured at 1.0MHz and applied reverse voltage of 4.0Vdc
 3. Thermal resistance junction to ambient & junction to terminals, 0.24"x0.24" (6.0x6.0mm) copper pads to each terminal.

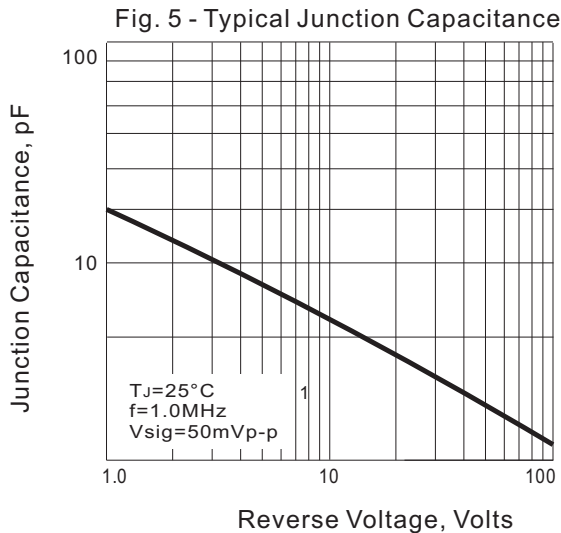
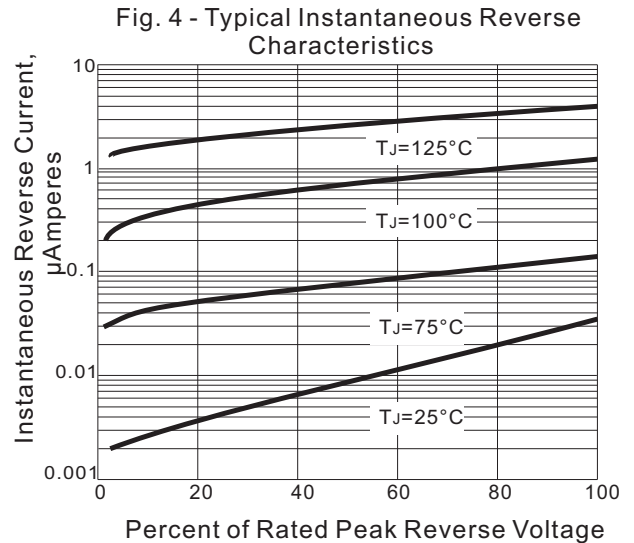
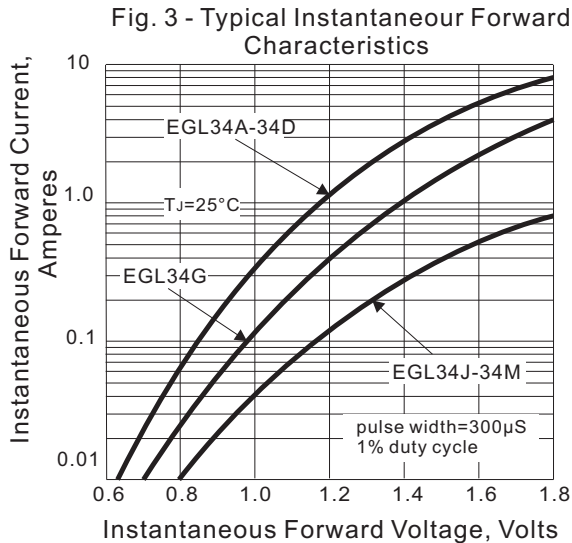
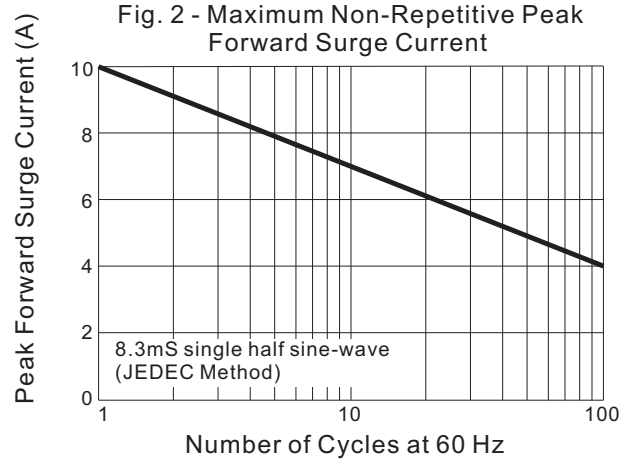
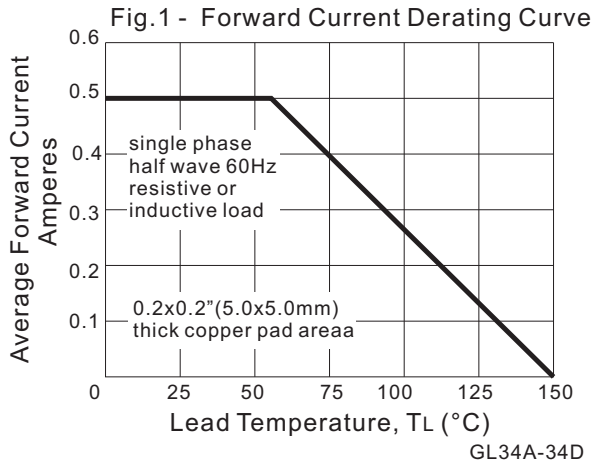
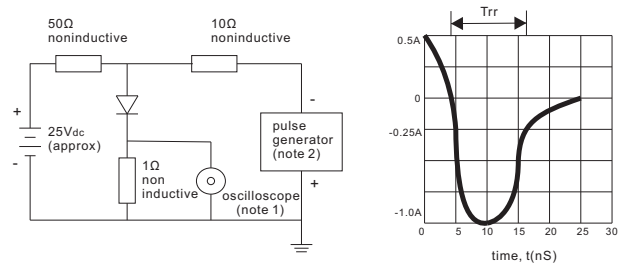


Fig. 6 - Test Circuit Diagram and Reverse Recovery Time Characteristic



Note: 1. rise time=7nS Max. input impedance=1MHz 22pF
 2. rise time=10nS Max. source impedance=80 Ω